

**KSC2758****NPN EPITAXIAL SILICON TRANSISTOR****RF. MIXER FOR UHF TUNER**

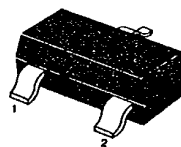
- HIGH POWER GAIN TYP. 17dB
- LOW NF TYP. 2.8dB

**ABSOLUTE MAXIMUM RATINGS ( $T_a = 25^\circ\text{C}$ )**

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	$V_{CB0}$	30	V
Collector-Emitter Voltage	$V_{CE0}$	25	V
Emitter-Base Voltage	$V_{EB0}$	4	V
Collector Current (DC)	$I_C$	20	mA
Collector Dissipation	$P_C$	150	mW
Junction Temperature	$T_J$	150	$^\circ\text{C}$
Storage Temperature	$T_{stg}$	-55 - 150	$^\circ\text{C}$

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1. Base 2. Emitter 3. Collector

**ELECTRICAL CHARACTERISTICS ( $T_a = 25^\circ\text{C}$ )**

Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
Collector Cutoff Current	$I_{CBO}$	$V_{CB} = 25\text{V}, I_E = 0$			0.1	$\mu\text{A}$
DC Current Gain	$h_{FE}$	$V_{CE} = 10\text{V}, I_C = 3\text{mA}$	60	120	240	
Current Gain Bandwidth Product	$f_T$	$V_{CE} = 10\text{V}, I_E = -3\text{mA}$	750	1000		MHz
Output Capacitance	$C_{ob}$	$f = 1\text{MHz}, V_{CB} = 10\text{V}, I_E = 0$		0.6	0.8	pF
Noise Figure	NF	$V_{CB} = 10\text{V}, I_E = -3\text{mA}$ $f = 900\text{MHz}$		2.8	4.5	dB
Power Gain	$G_{pb}$	$V_{CB} = 10\text{V}, I_E = -3\text{mA}$ $f = 900\text{MHz}$	14	17		dB
AGC Current	$I_{AGC}$	$G_{pb} \text{ AGC} = I_E \text{ of } G_{pb} - 30\text{dB}$		-8	-11	mA

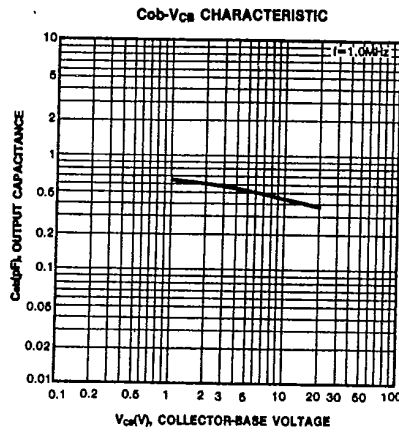
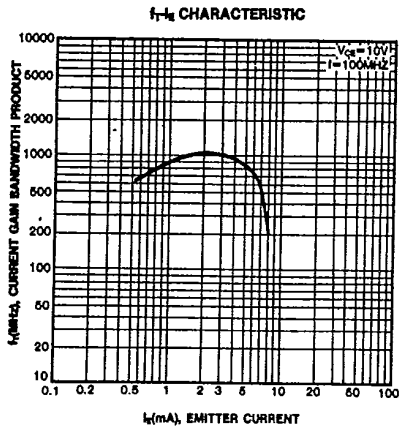
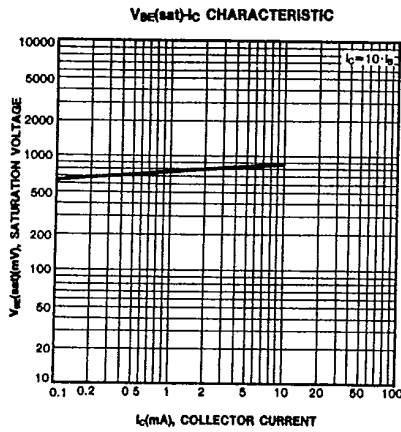
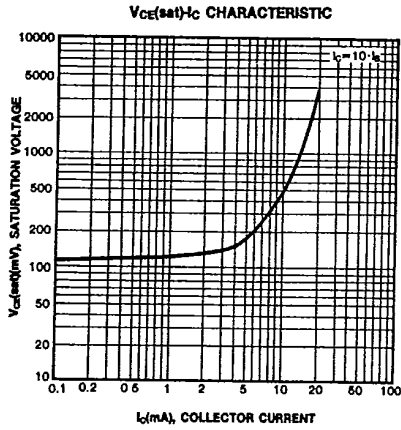
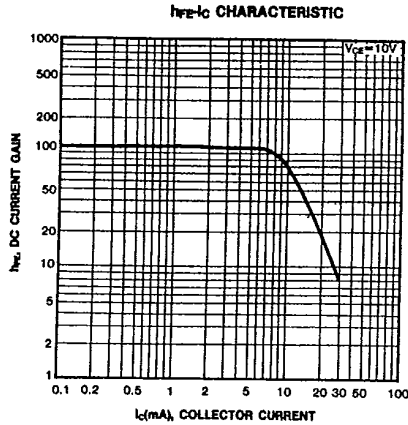
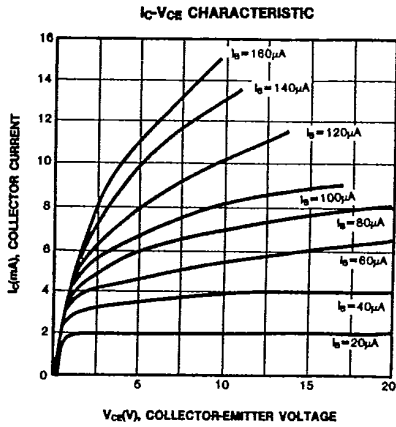
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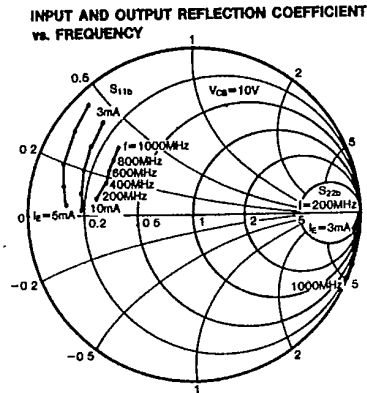
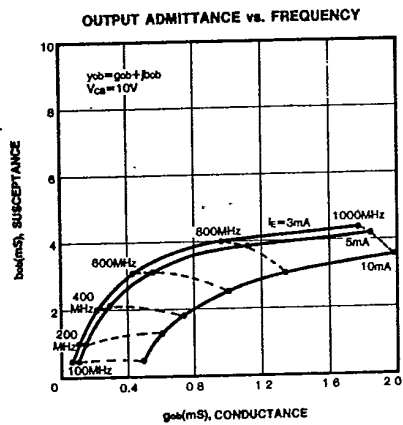
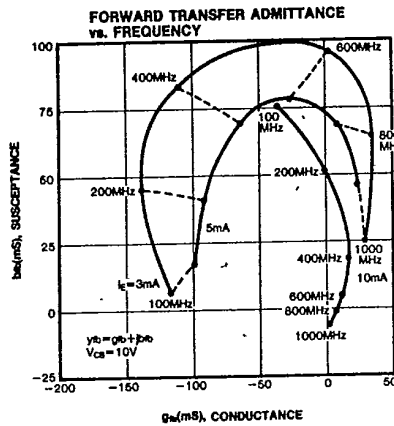
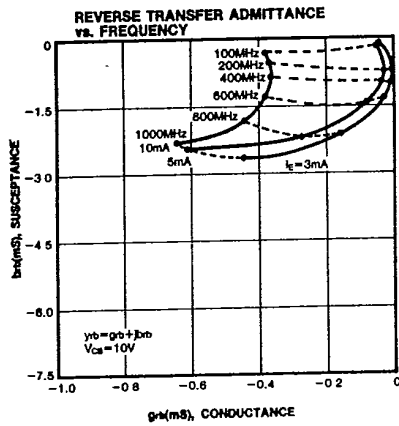
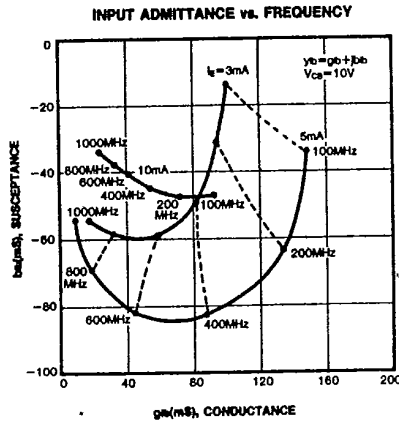
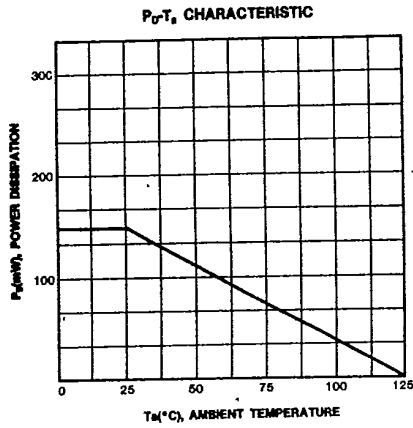


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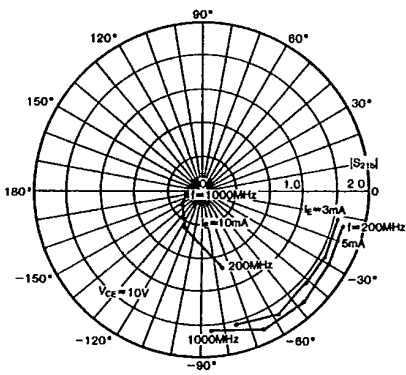


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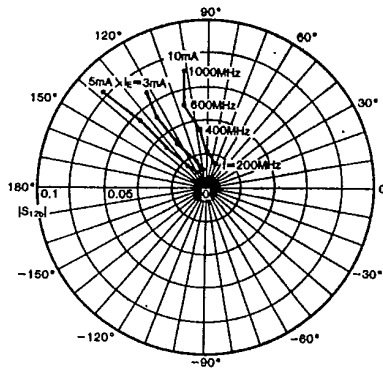
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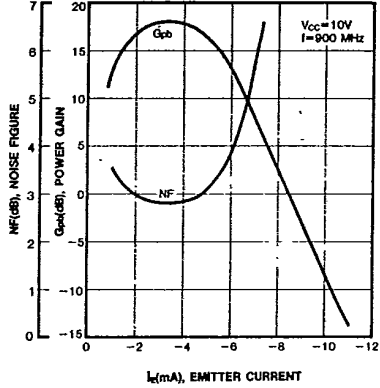
FORWARD INSERTION GAIN vs. FREQUENCY



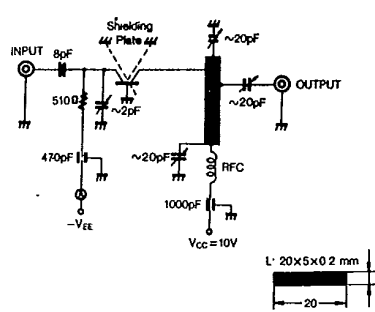
REVERSE INSERTION GAIN vs. FREQUENCY



POWER GAIN AND NOISE FIGURE vs. COLLECTOR CURRENT



900 MHz Gp, NF TEST CIRCUIT



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